

Vishay Semiconductors

Small Signal Switching Diode

Features

- · Silicon Epitaxial Planar Diode
- · Low forward voltage drop
- High forward current capability
- AEC-Q101 qualified
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition









Applications

· High speed switch and general purpose use in computer and industrial applications

Mechanical Data

Case: DO-35

Weight: approx. 125 mg Cathode Band Color: black **Packaging Codes/Options:**

TR/10 k per 13" reel (52 mm tape), 50 k/box TAP/10 k per Ammopack (52 mm tape), 50 k/box

Parts Table

Part	Ordering code	Type Marking	Remarks
BAW27	BAW27-TR or BAW27-TAP	BAW27	Tape and Reel/Ammopack

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Repetitive peak reverse voltage		V _{RRM}	75	V
Reverse voltage		V _R	60	V
Peak forward surge current	t _p = 1 μs	I _{FSM}	4	Α
Forward continuous current		I _F	600	mA
Average forward current	V _R = 0	I _{FAV}	300	mA
Power dissipation	I = 4 mm, T _L = 45 °C	P _{tot}	440	mW
	$I = 4$ mm, $T_L \le 25$ °C	P _{tot}	500	mW

Thermal Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air	I = 4 mm, T _L = constant	R _{thJA} 350		K/W
Junction temperature		Tj	175	°C
Storage temperature range		T _{stg}	- 65 to + 175	°C

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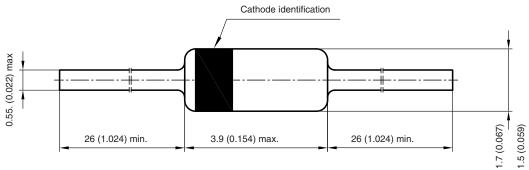


Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min.	Тур.	Max.	Unit
Forward voltage	I _F = 10 mA	V _F		670	750	mV
	I _F = 50 mA	V _F		800	850	mV
	I _F = 200 mA	V _F		950	1000	mV
	I _F = 400 mA	V _F		1120	1250	mV
Reverse current	V _R = 60 V	I _R			100	nA
	$V_R = 60 \text{ V}, T_j = 100 ^{\circ}\text{C}$	I _R			50	μΑ
Breakdown voltage	$I_R = 5 \mu A, t_p/T = 0.01,$ $t_p = 0.3 \text{ ms}$	V _(BR)	75			V
Diode capacitance	$V_R = 0$, $f = 1$ MHz, $V_{HF} = 50$ mV	C _D			4	pF
Reverse recovery time	$I_F = I_R = 10 \text{ mA to } 100 \text{ mA},$ $I_R = 0.1 \times I_R$	t _{rr}			6	ns

Package Dimensions in millimeters (inches): DO-35



Rev. 6 - Date: 29. January 2007 Document no.: 6.560-5004.02-4

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Document Number: 91000 Revision: 18-Jul-08

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